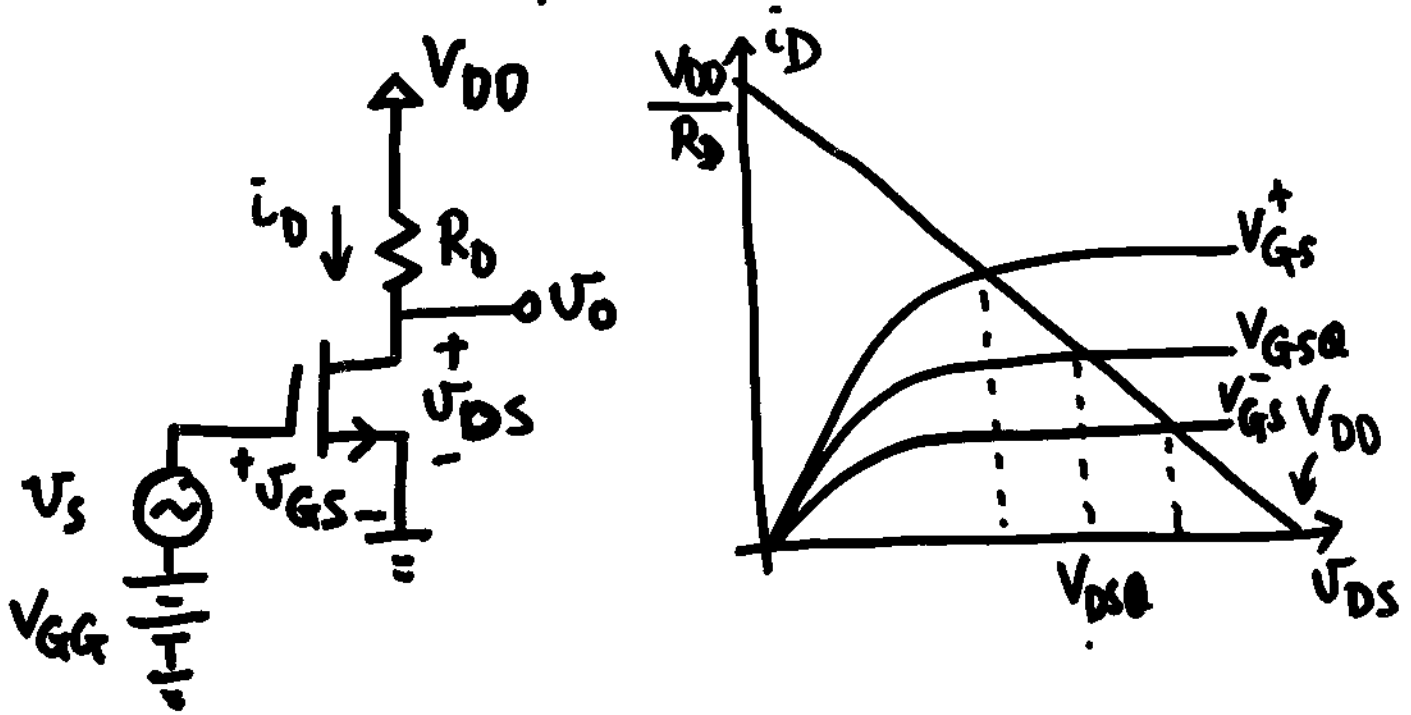


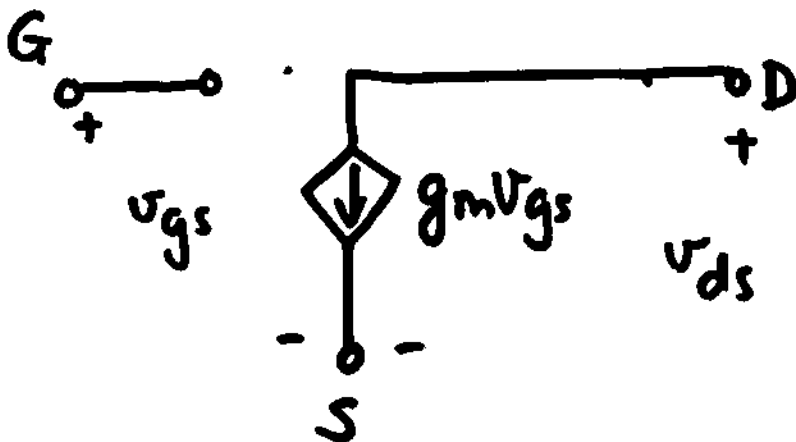
MOSFET Amplifiers



SATURATION:

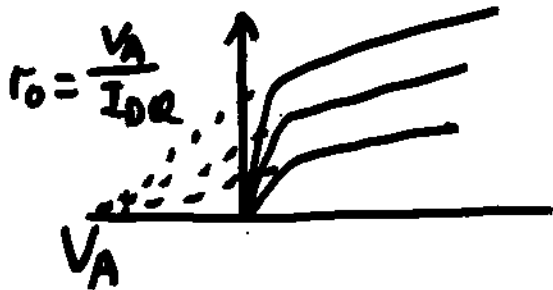
$$i_D = K_N (V_{GS} - V_{TH})^2$$

$$\approx \underbrace{K_N (V_{GSQ} - V_{TH})^2}_{I_{DQ}} + \underbrace{2K_N (V_{GSQ} - V_{TH}) v_{gs}}_{i_d = g_m v_{gs}}$$



Channel length modulation

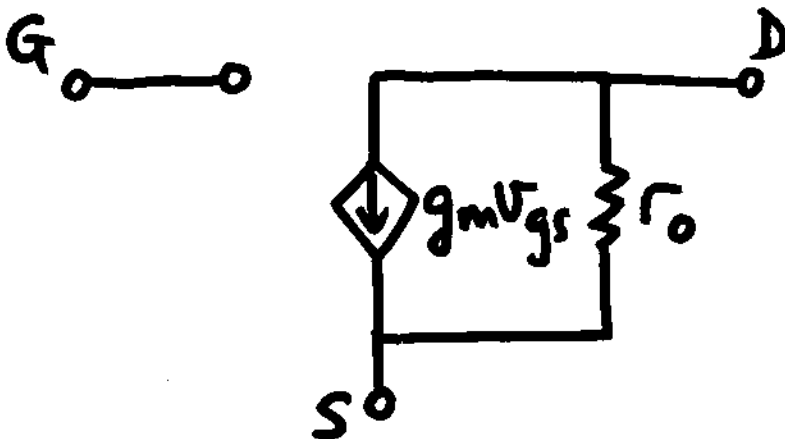
$$I_D = K_N (V_{GS} - V_{TH})^2 (1 + \lambda V_{DS})$$



↑
channel length
modulation factor

Incremental drain-to-source resistance

$$r_o = r_{ds} = \left. \frac{\partial V_{DS}}{\partial I_D} \right|_{V_{GSQ}} = \frac{1}{\lambda K_N (V_{GSQ} - V_{TH})^2}$$



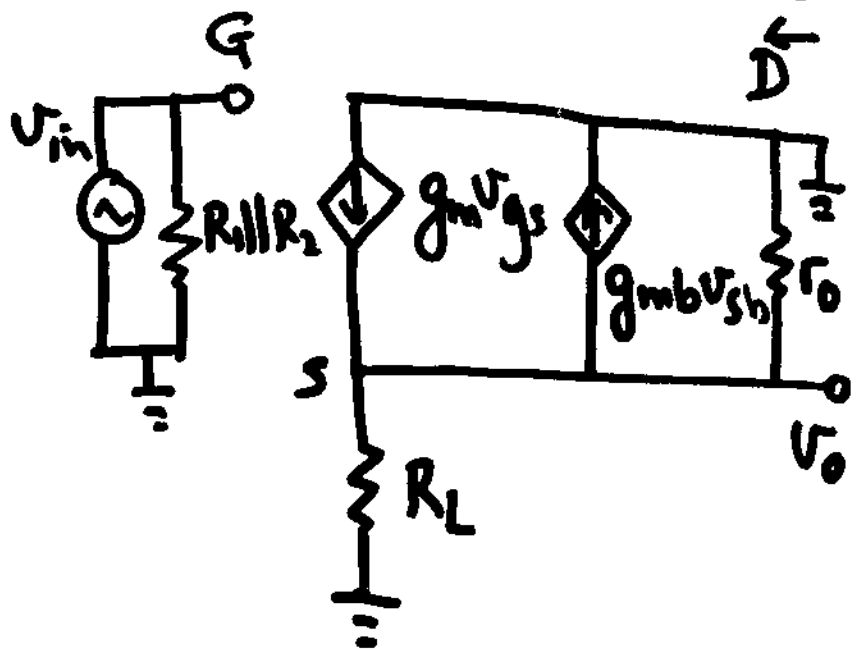
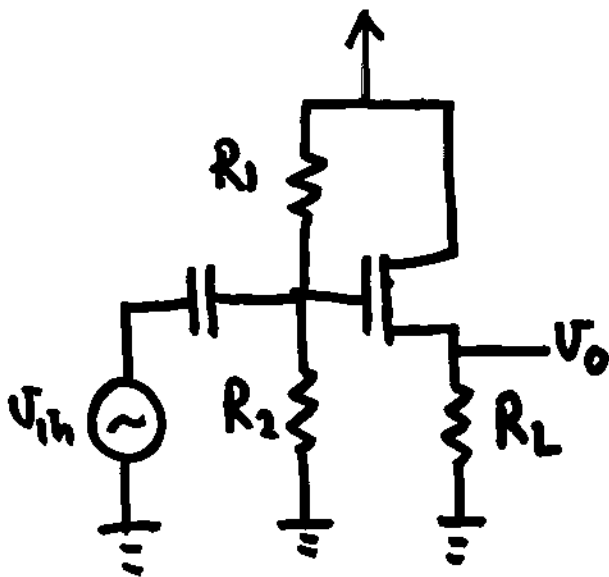
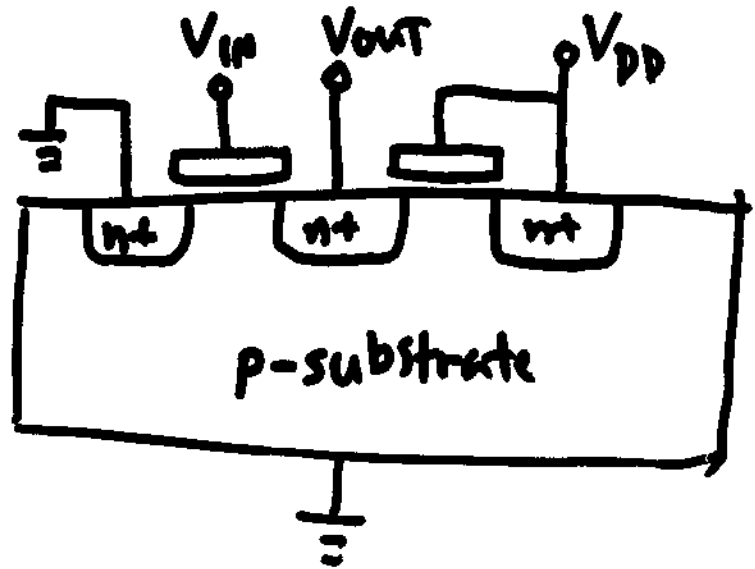
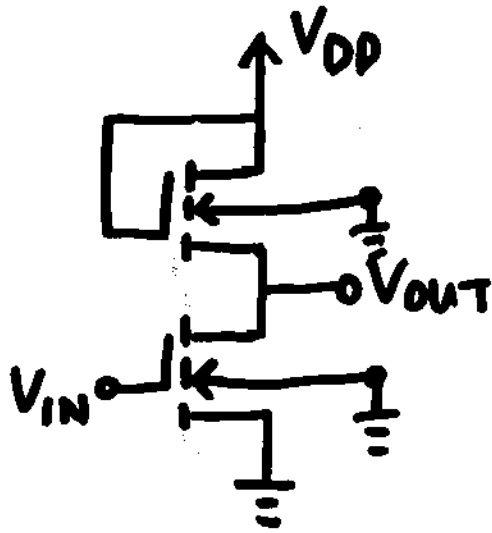
Should g_m change according?

YES : $g_m = 2K_N (V_{GSQ} - V_{TH}) (1 + \lambda V_{DSQ})$

But typically ignored

Body effect

$$V_{TH} = V_{TH0} + \gamma \left[\sqrt{2\phi_f + V_{SB}} - \sqrt{2\phi_f} \right]$$



$$\begin{aligned}
 g_{mb} &= \left. \frac{\partial I_D}{\partial V_{SB}} \right|_{Q\text{-pt}} \\
 &= \left. \frac{\partial I_D}{\partial V_{TH}} \cdot \frac{\partial V_{TH}}{\partial V_{SB}} \right|_{Q\text{-pt}} \\
 &= -2 K_N (V_{GSQ} - V_{TH}) \cdot \frac{\gamma}{2\sqrt{2\phi_f + V_{SBQ}}} \\
 &= -g_m \frac{\gamma}{\sqrt{2\phi_f + V_{SBQ}}}
 \end{aligned}$$

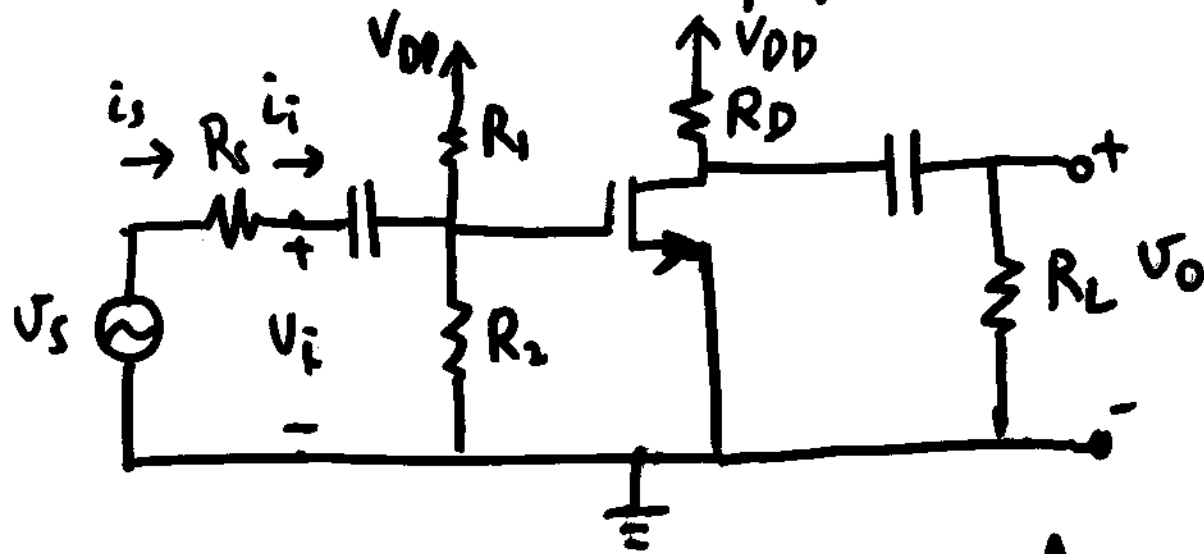
$$V_{SB} > 0$$

$\Rightarrow V_{SB}$ increases

$\Rightarrow V_{TH}$ increases

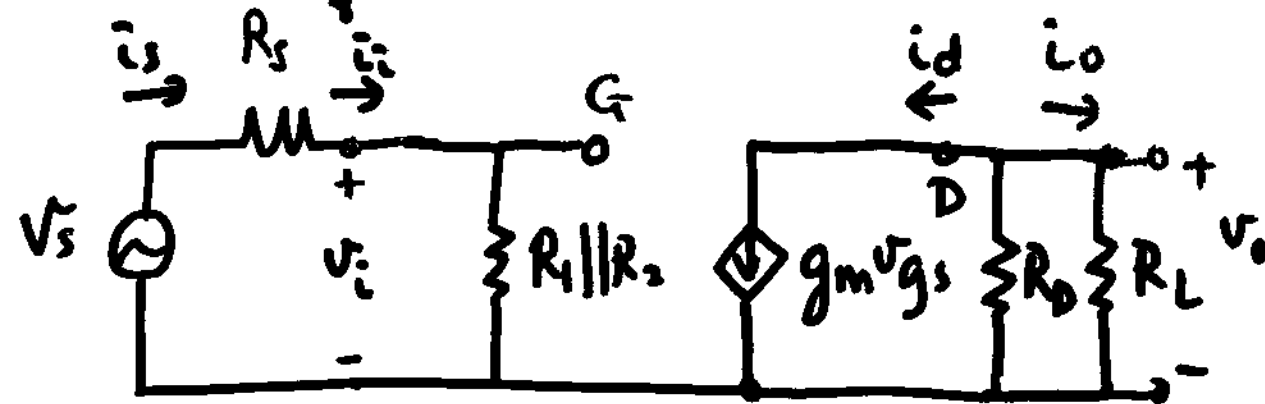
$\Rightarrow I_D$ decreases

Common-Source Amplifier



Assume $r_o = \infty$

a.c. equivalent circuit



$$v_o = -g_m v_{gs} (R_D \parallel R_L)$$

$$v_i = v_{gs}$$

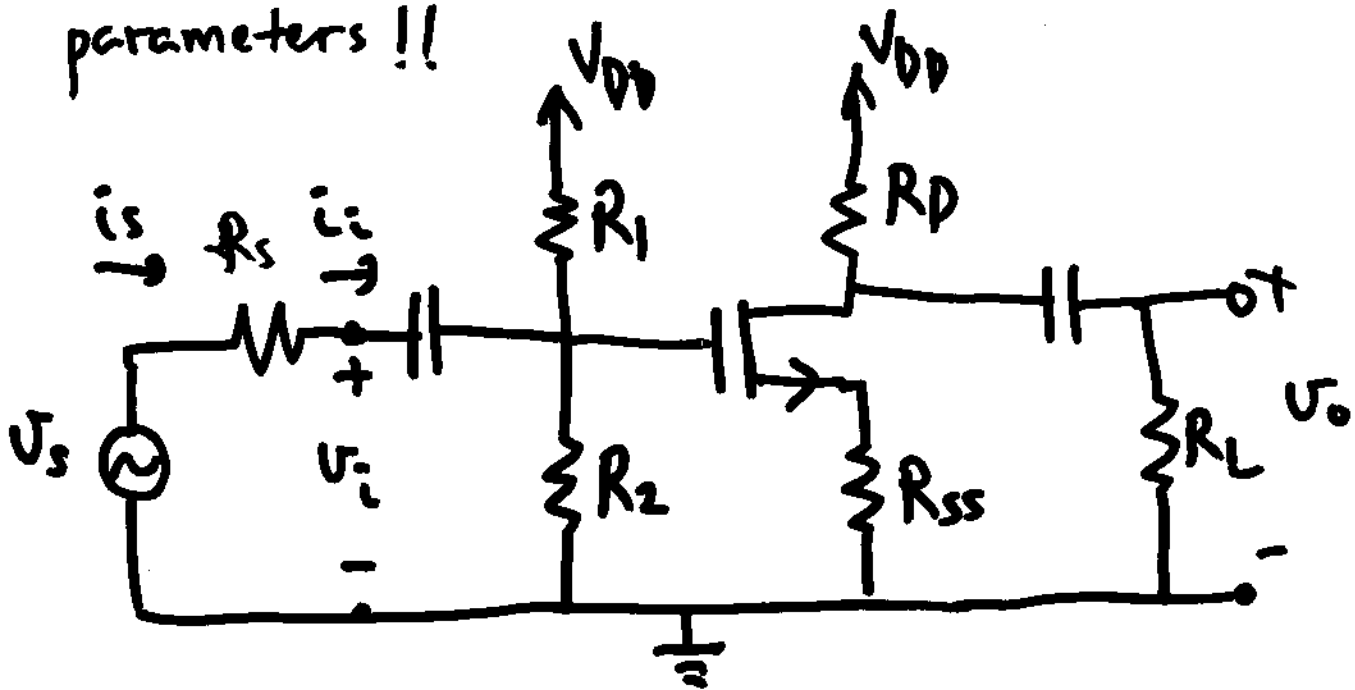
$$A_{v_i} = -g_m (R_D \parallel R_L)$$

$$A_{i_i} = \frac{v_o / R_L}{v_i / R_{in}} = A_{v_i} \frac{R_1 \parallel R_2}{R_L}$$

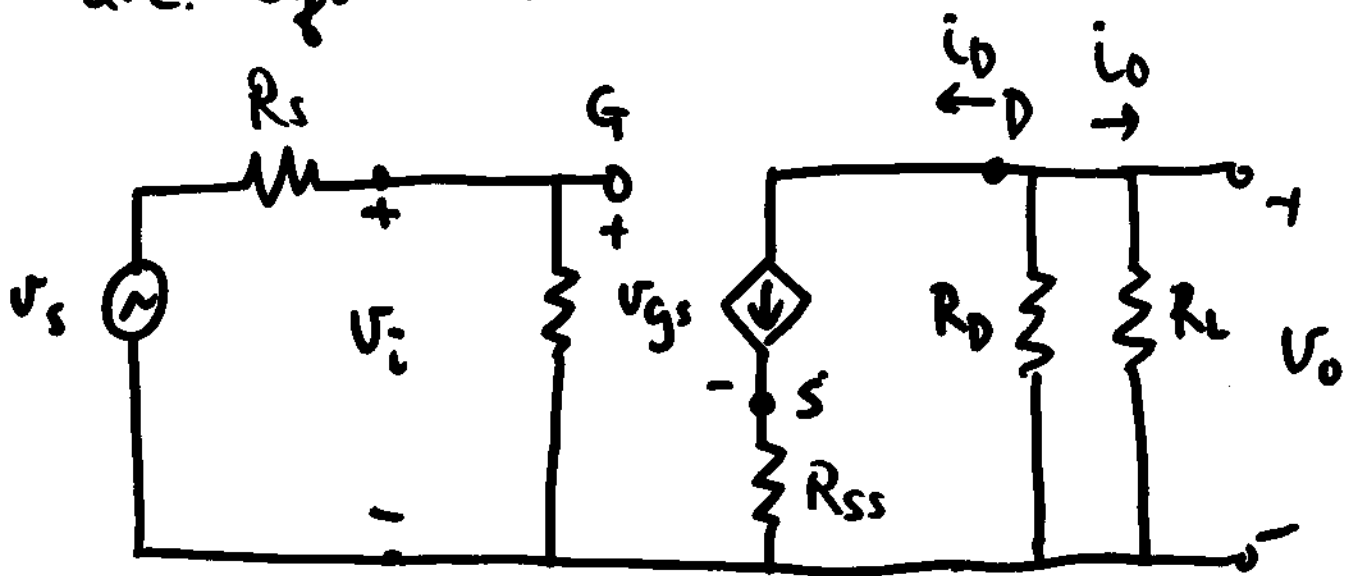
$$A_{p_i} = A_{i_i} A_{v_i} = A_{v_i}^2 \frac{R_1 \parallel R_2}{R_L}$$

Just like
CE BJT Amp!!
 $g_{mFET} < g_{mBJT}$

Add source degeneration resistor
to stabilize against variations in transistor
parameters !!



a.c. equivalent circuit



$$V_o = -g_m V_{gs} (R_D \parallel R_L)$$

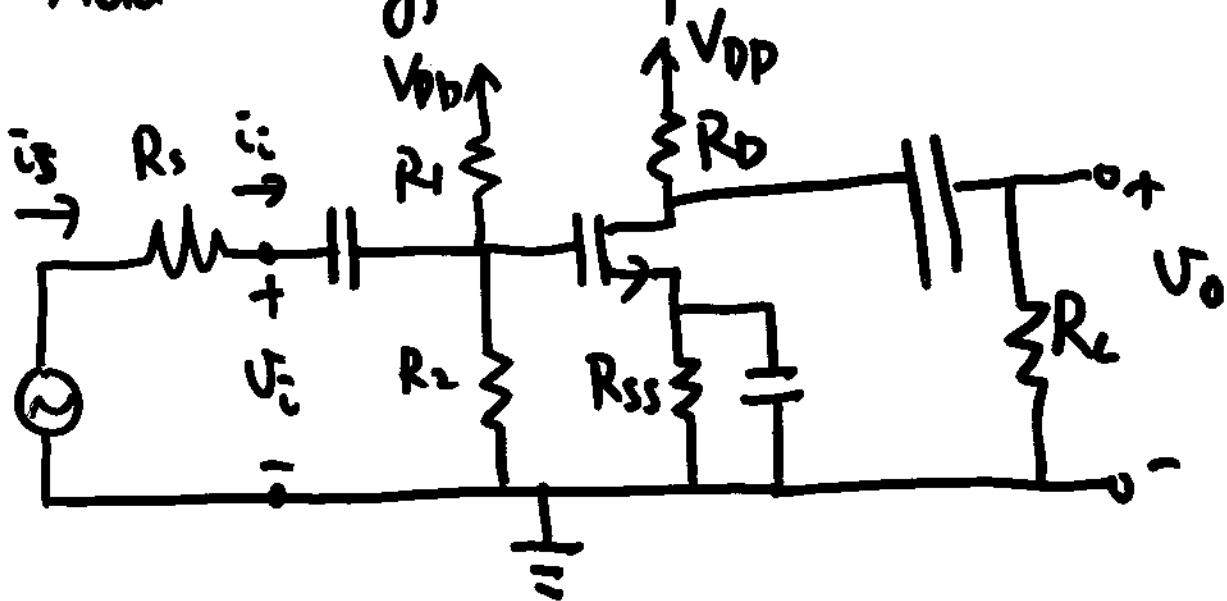
$$V_i = V_{gs} + g_m V_{gs} R_{SS}$$

$$= V_{gs} (1 + g_m R_{SS})$$

$$A_{V_i} = \frac{-g_m (R_D \parallel R_L)}{1 + g_m R_{SS}}$$

STABLE BUT LOW GAIN

Add a bypass capacitor



BJT - MOSFET Analogy

C.E. C.S.

BJT

$$v_o = -g_m v_{\pi} (R_c \parallel R_L)$$

$$v_i = v_{\pi} + (\beta + 1) i_b R_E$$

$$= v_{\pi} + (\beta + 1) \frac{v_{\pi}}{r_{\pi}} R_E$$

$$A_{v_i \text{ BJT}} = \frac{-g_m (R_c \parallel R_L)}{1 + \frac{(\beta + 1) R_E}{r_{\pi}}} \quad \text{--- } \textcircled{1}$$

$\beta \rightarrow \infty$, $r_{\pi} \rightarrow \infty$, $\beta / r_{\pi} \rightarrow g_m$, $R_c \rightarrow R_D$
 $R_E \rightarrow R_{SS}$

$\textcircled{1}$ becomes

$$\frac{-g_m (R_c \parallel R_L)}{1 + \frac{(\beta + 1) R_E}{r_{\pi}}}$$
$$= \frac{-g_m (R_D \parallel R_L)}{1 + g_m R_E}$$